

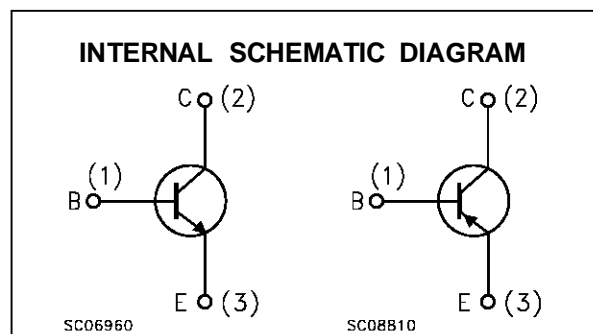
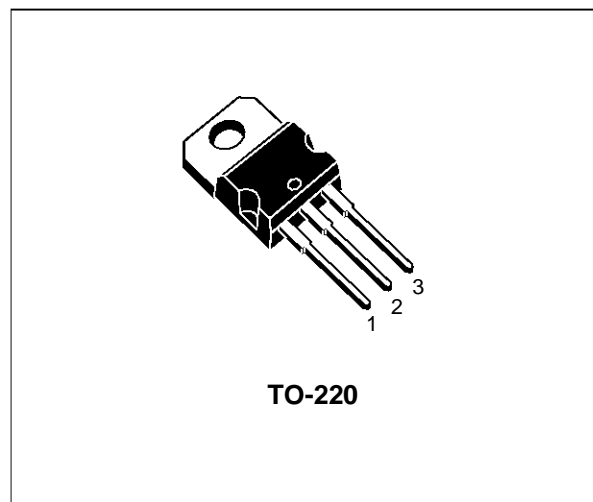
## COMPLEMENTARY SILICON POWER TRANSISTORS

- BD534, BD535, BD536, BD537 AND BD538 ARE SGS-THOMSON PREFERRED SALESTYPE

### DESCRIPTION

The BD533, BD535, and BD537 are silicon epitaxial-base NPN power transistors in Jedec TO-220 plastic package, intended for use in medium power linear and switching applications.

The complementary PNP types are BD534, BD536, and BD538 respectively.



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value				Unit
		NPN	BD533	BD535	BD537	
		PNP	BD534	BD536	BD538	
$V_{CBO}$	Collector-Base Voltage ( $I_E = 0$ )		45	60	80	V
$V_{CES}$	Collector-Emitter Voltage ( $V_{BE} = 0$ )		45	60	80	V
$V_{CEO}$	Collector-Emitter Voltage ( $I_B = 0$ )		45	60	80	V
$V_{EBO}$	Emitter-Base Voltage ( $I_C = 0$ )			5		V
$I_C, I_E$	Collector and Emitter Current			8		A
$I_B$	Base Current			1		A
$P_{tot}$	Total Dissipation at $T_c \leq 25^\circ\text{C}$			50		W
$T_{stg}$	Storage Temperature			-65 to 150		$^\circ\text{C}$
$T_j$	Max. Operating Junction Temperature			150		$^\circ\text{C}$

For PNP types voltage and current values are negative.

## BD533/BD534/BD535/BD536/BD537/BD538

### THERMAL DATA

R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max	2.5	°C/W
R <sub>thj-amb</sub>	Thermal Resistance Junction-ambient	Max	70	°C/W

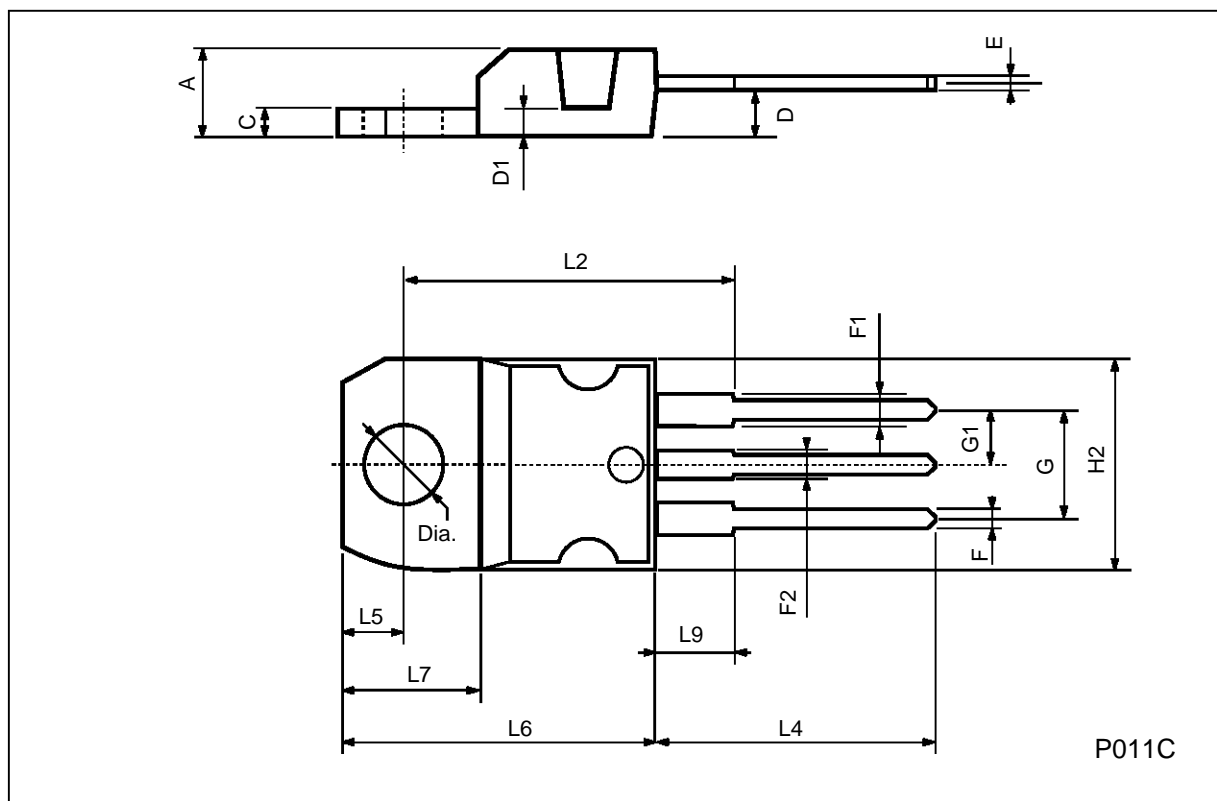
### ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I <sub>CBO</sub>	Collector Cut-off Current (I <sub>E</sub> = 0)	for <b>BD533/534</b> V <sub>CB</sub> = 45 V for <b>BD535/536</b> V <sub>CB</sub> = 60 V for <b>BD537/538</b> V <sub>CB</sub> = 80 V			100 100 100	μA μA μA
I <sub>CES</sub>	Collector Cut-off Current (V <sub>BE</sub> = 0)	for <b>BD533/534</b> V <sub>CB</sub> = 45 V for <b>BD535/536</b> V <sub>CB</sub> = 60 V for <b>BD537/538</b> V <sub>CB</sub> = 80 V			100 100 100	μA μA μA
I <sub>EBO</sub>	Emitter Cut-off Current (I <sub>C</sub> = 0)	V <sub>EB</sub> = 5 V			1	mA
V <sub>CEO(sus)*</sub>	Collector-Emitter Sustaining Voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 100 mA	for <b>BD533/534</b> 45 for <b>BD535/536</b> 60 for <b>BD537/538</b> 80			V V V
V <sub>CE(sat)*</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2 A I <sub>C</sub> = 6 A	I <sub>B</sub> = 0.2 A I <sub>B</sub> = 0.6 A	0.8	0.8	V V
V <sub>BE*</sub>	Base-Emitter Voltage	I <sub>C</sub> = 2 A	V <sub>CE</sub> = 2 V		1.5	V
h <sub>FE*</sub>	DC Current Gain	I <sub>C</sub> = 10 mA  I <sub>C</sub> = 500 mA I <sub>C</sub> = 2 A	V <sub>CE</sub> = 5 V for <b>BD533/534</b> for <b>BD535/536</b> for <b>BD537/538</b> V <sub>CE</sub> = 2 V V <sub>CE</sub> = 2 V for <b>BD533/534</b> for <b>BD535/536</b> for <b>BD537/538</b>	20 20 15 40 25 25 15		
f <sub>T</sub>	Transition frequency	I <sub>C</sub> = 500 mA	V <sub>CE</sub> = 1 V	3	12	MHz

\* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %  
For PNP types voltage and current values are negative.

**TO-220 MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



Information furnished is believed to be accurate and reliable. However, SGS-THOMSON Microelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of SGS-THOMSON Microelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. SGS-THOMSON Microelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of SGS-THOMSON Microelectronics.

© 1995 SGS-THOMSON Microelectronics - All Rights Reserved

SGS-THOMSON Microelectronics GROUP OF COMPANIES

Australia - Brazil - France - Germany - Hong Kong - Italy - Japan - Korea - Malaysia - Malta - Morocco - The Netherlands - Singapore - Spain - Sweden - Switzerland - Taiwan - Thailand - United Kingdom - U.S.A